

# PSMN1R5-50YLH

N-channel 50 V, 1.7 mOhm, 200 A continuous, logic level Application Specific MOSFET in LFPAK56E

**26 January 2022** 

**Product data sheet** 

## 1. General description

200 Amp continuous current, logic level gate drive, N-channel enhancement mode MOSFET in LFPAK56E package. Part of the ASFETs for Battery Isolation and DC Motor control family and using Nexperia's unique "SchottkyPlus" technology delivers high efficiency and low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. The ASFET is particularly suited to 36 V battery powered applications requiring strong avalanche capability, linear mode performance, use at high switching frequencies, and also safe and reliable switching at high load-current.

### 2. Features and benefits

- 200 A continuous current capability
- Optimised for 36 V (nominal) battery powered applications
- LFPAK56E low-stress exposed lead-frame for ultimate reliability, optimum soldering and easy solder-joint inspection
- Copper-clip and solder die attach for low package inductance and resistance, and high I<sub>D (max)</sub> rating
- Qualified to 175 °C
- Avalanche rated, 100% tested
- Low Q<sub>G</sub>, Q<sub>GD</sub> and Q<sub>OSS</sub> for high efficiency, especially at higher switching frequencies
- Superfast switching with soft body-diode recovery for low-spiking and ringing, recommended for low EMI designs
- Unique "SchottkyPlus" technology for Schottky-like switching performance and low I<sub>DSS</sub> leakage
- Narrow V<sub>GS(th)</sub> rating for easy paralleling and improved current sharing
- Very strong linear-mode / safe operating area characteristics for safe and reliable switching at high-current conditions

# 3. Applications

- Brushless DC motor control
- Synchronous rectifier in high-power AC-to-DC applications, e.g. server power supplies
- Battery protection and Battery Management Systems (BMS)
- · Load switch
- 10 cell lithium-ion battery applications (36 V 42 V)

#### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol           | Parameter               | Conditions                                                     |     | Min | Тур | Max | Unit |
|------------------|-------------------------|----------------------------------------------------------------|-----|-----|-----|-----|------|
| V <sub>DS</sub>  | drain-source voltage    | 25 °C ≤ T <sub>j</sub> ≤ 175 °C                                |     | -   | -   | 50  | V    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u> | [1] | -   | -   | 200 | Α    |
| P <sub>tot</sub> | total power dissipation | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>                         |     | -   | -   | 333 | W    |
| T <sub>j</sub>   | junction temperature    |                                                                |     | -55 | -   | 175 | °C   |



| Symbol              | Parameter                        | Conditions                                                              |   | Min | Тур | Max  | Unit |  |
|---------------------|----------------------------------|-------------------------------------------------------------------------|---|-----|-----|------|------|--|
| Static charact      | Static characteristics           |                                                                         |   |     |     |      |      |  |
| R <sub>DSon</sub>   | drain-source on-state resistance | $V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C;<br>Fig. 10            |   | -   | 1.4 | 1.75 | mΩ   |  |
|                     |                                  | $V_{GS}$ = 4.5 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C;<br>Fig. 10           |   | -   | 1.6 | 2    | mΩ   |  |
| Dynamic char        | acteristics                      |                                                                         | • |     |     |      | ·    |  |
| $Q_{GD}$            | gate-drain charge                | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 4.5 V; |   | -   | 13  | 29   | nC   |  |
| Q <sub>G(tot)</sub> | total gate charge                | Fig. 12; Fig. 13                                                        |   | -   | 53  | 82   | nC   |  |

<sup>[1] 200</sup>A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description                       | Simplified outline                           | Graphic symbol |
|-----|--------|-----------------------------------|----------------------------------------------|----------------|
| 1   | S      | source                            |                                              |                |
| 2   | S      | source                            |                                              |                |
| 3   | S      | source                            |                                              | D              |
| 4   | G      | gate                              |                                              |                |
| mb  | D      | mounting base; connected to drain | 1 2 3 4<br>LFPAK56E; Power-<br>SO8 (SOT1023) | mbb076 S       |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number   | Package |                                                                                 |         |  |  |
|---------------|---------|---------------------------------------------------------------------------------|---------|--|--|
|               | Name    | Description                                                                     | Version |  |  |
| PSMN1R5-50YLH | ,       | plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch | SOT1023 |  |  |

## 7. Marking

#### Table 4. Marking codes

| Type number   | Marking code |
|---------------|--------------|
| PSMN1R5-50YLH | 1H550L       |

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

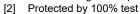
| Symbol    | Parameter            | Conditions                               | Min | Max | Unit |
|-----------|----------------------|------------------------------------------|-----|-----|------|
| $V_{DS}$  | drain-source voltage | 25 °C ≤ T <sub>j</sub> ≤ 175 °C          | -   | 50  | V    |
| $V_{DGR}$ | drain-gate voltage   | 25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ | -   | 50  | V    |

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| Symbol               | Parameter                                        | Conditions                                                                                                         |     | Min | Max  | Unit |
|----------------------|--------------------------------------------------|--------------------------------------------------------------------------------------------------------------------|-----|-----|------|------|
| V <sub>GS</sub>      | gate-source voltage                              |                                                                                                                    |     | -20 | 20   | V    |
| P <sub>tot</sub>     | total power dissipation                          | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>                                                                             |     | -   | 333  | W    |
| I <sub>D</sub>       | drain current                                    | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>                                                     | [1] | -   | 200  | А    |
|                      |                                                  | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>                                                    |     | -   | 200  | Α    |
| I <sub>DM</sub>      | peak drain current                               | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; Fig. 3                                                     |     | -   | 1159 | А    |
| T <sub>stg</sub>     | storage temperature                              |                                                                                                                    |     | -55 | 175  | °C   |
| Tj                   | junction temperature                             |                                                                                                                    |     | -55 | 175  | °C   |
| $T_{sld(M)}$         | peak soldering temperature                       |                                                                                                                    |     | -   | 260  | °C   |
| Source-drain         | diode                                            |                                                                                                                    | 1   |     |      |      |
| Is                   | source current                                   | T <sub>mb</sub> = 25 °C                                                                                            |     | -   | 200  | Α    |
| I <sub>SM</sub>      | peak source current                              | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$                                                                      |     | -   | 1159 | Α    |
| Avalanche ruç        | ggedness                                         |                                                                                                                    |     | ,   |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche energy | $I_D$ = 50 A; $V_{sup}$ ≤ 50 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 513 μs | [2] | -   | 833  | mJ   |
|                      |                                                  | $I_D$ = 25 A; $V_{sup}$ ≤ 50 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 2.5 ms | [2] | -   | 2    | J    |
| I <sub>AS</sub>      | non-repetitive avalanche current                 | $V_{sup} \le 50 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$<br>$R_{GS} = 50 \Omega$            | [2] | -   | 115  | Α    |

<sup>[1] 200</sup>A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.



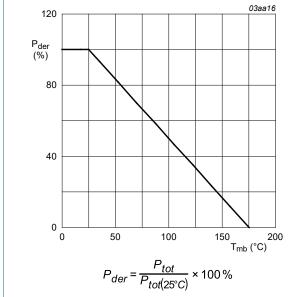
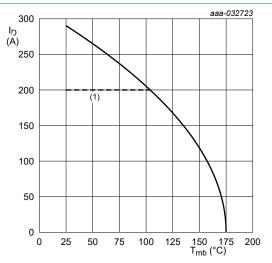
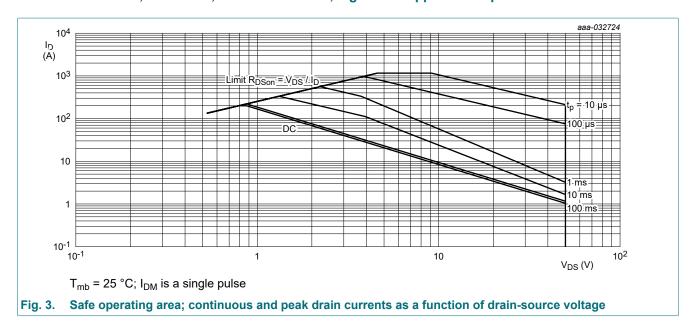


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$  (1) 200A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

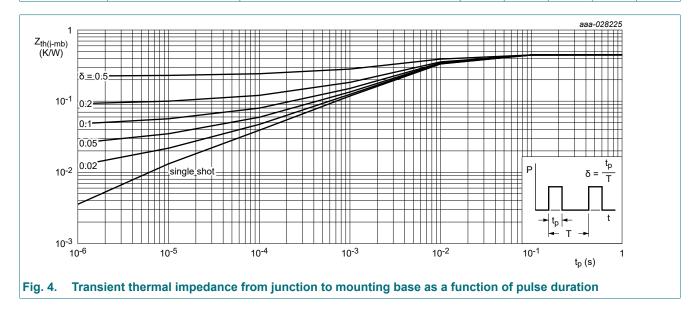
Fig. 2. Continuous drain current as a function of mounting base temperature

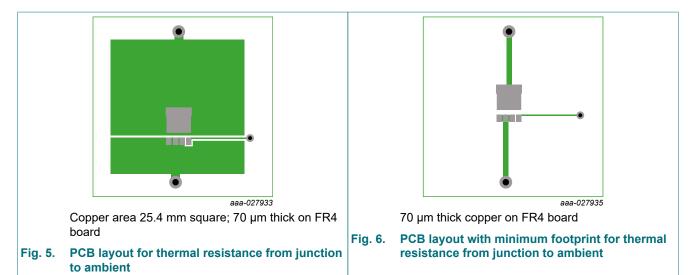


### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                                                           | Parameter                                         | Conditions    | Min | Тур  | Max  | Unit |
|------------------------------------------------------------------|---------------------------------------------------|---------------|-----|------|------|------|
| R <sub>th(j-mb)</sub>                                            | thermal resistance from junction to mounting base | Fig. 4        | -   | 0.33 | 0.45 | K/W  |
| R <sub>th(j-a)</sub> thermal resistance from junction to ambient | thermal resistance from                           | Fig. <u>5</u> | -   | 42   | -    | K/W  |
|                                                                  | Fig. 6                                            | -             | 85  | -    | K/W  |      |





## 10. Characteristics

**Table 7. Characteristics** 

| Symbol                       | Parameter                                                | Conditions                                                                                  | Min  | Тур  | Max  | Unit |
|------------------------------|----------------------------------------------------------|---------------------------------------------------------------------------------------------|------|------|------|------|
| Static charac                | teristics                                                |                                                                                             |      | '    |      |      |
| V <sub>(BR)DSS</sub>         | drain-source                                             | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                      | 50   | -    | -    | V    |
|                              | breakdown voltage                                        | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$                                               | 45   | -    | -    | V    |
| V <sub>GS(th)</sub>          | gate-source threshold voltage                            | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                                  | 1.2  | 1.61 | 2.2  | V    |
| $\Delta V_{GS(th)}/\Delta T$ | gate-source threshold voltage variation with temperature | 25 °C ≤ T <sub>j</sub> ≤ 150 °C                                                             | -    | -4.6 | -    | mV/K |
| I <sub>DSS</sub>             | drain leakage current                                    | V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                       | -    | 0.01 | 1    | μΑ   |
|                              |                                                          | V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C                      | -    | 3.9  | -    | μΑ   |
| I <sub>GSS</sub>             | gate leakage current                                     | V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                       | -    | 2    | 100  | nA   |
|                              |                                                          | V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                      | -    | 2    | 100  | nA   |
| R <sub>DSon</sub>            | drain-source on-state resistance                         | $V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C;<br>Fig. 10                                    | -    | 1.4  | 1.75 | mΩ   |
|                              |                                                          | $V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 150 °C;<br>Fig. 11                                   | -    | -    | 3.52 | mΩ   |
|                              |                                                          | $V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 25 °C;<br>Fig. 10                                   | -    | 1.6  | 2    | mΩ   |
|                              |                                                          | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C;<br>Fig. 11         | -    | -    | 4.02 | mΩ   |
| R <sub>G</sub>               | gate resistance                                          | f = 1 MHz; T <sub>j</sub> = 25 °C                                                           | 0.52 | 1.3  | 3.3  | Ω    |
| Dynamic cha                  | racteristics                                             |                                                                                             |      |      |      |      |
| Q <sub>G(tot)</sub>          | total gate charge                                        | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 4.5 V;<br>Fig. 12; Fig. 13 | -    | 53   | 82   | nC   |
|                              |                                                          | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 10 V;<br>Fig. 12; Fig. 13  | -    | 117  | 181  | nC   |
|                              |                                                          | I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V                         | -    | 61   | -    | nC   |

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| Symbol                 | Parameter                             | Conditions                                                                                 |     | Min | Тур      | Max      | Unit |
|------------------------|---------------------------------------|--------------------------------------------------------------------------------------------|-----|-----|----------|----------|------|
| Q <sub>GS</sub>        | gate-source charge                    | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 4.5 V;                    |     | -   | 17       | 26       | nC   |
| Q <sub>GS(th)</sub>    | pre-threshold gate-<br>source charge  | Fig. 12; Fig. 13                                                                           |     | -   | 11.3     | 17       | nC   |
| Q <sub>GS(th-pl)</sub> | post-threshold gate-<br>source charge |                                                                                            |     | -   | 5.4      | 8        | nC   |
| Q <sub>GD</sub>        | gate-drain charge                     |                                                                                            |     | -   | 13       | 29       | nC   |
| $V_{GS(pl)}$           | gate-source plateau voltage           | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 25 V; <u>Fig. 12</u> ; <u>Fig. 13</u>             |     | -   | 2.5      | -        | V    |
| C <sub>iss</sub>       | input capacitance                     | V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;                                  |     | -   | 7959     | 11143    | pF   |
| C <sub>oss</sub>       | output capacitance                    | T <sub>j</sub> = 25 °C; <u>Fig. 14</u>                                                     |     | -   | 799      | 1119     | pF   |
| C <sub>rss</sub>       | reverse transfer capacitance          |                                                                                            |     | -   | 231      | 554      | pF   |
| t <sub>d(on)</sub>     | turn-on delay time                    | $V_{DS} = 25 \text{ V}; R_L = 1 \Omega; V_{GS} = 4.5 \text{ V};$                           |     | -   | 39       | -        | ns   |
| t <sub>r</sub>         | rise time                             | $R_{G(ext)} = 5 \Omega$                                                                    |     | -   | 40       | -        | ns   |
| t <sub>d(off)</sub>    | turn-off delay time                   |                                                                                            |     | -   | 68       | -        | ns   |
| t <sub>f</sub>         | fall time                             |                                                                                            |     | -   | 32       | -        | ns   |
| Q <sub>oss</sub>       | output charge                         | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ °C}$ |     | -   | 42       | -        | nC   |
| Source-drai            | in diode                              |                                                                                            | •   |     | <u>'</u> | <u>'</u> |      |
| $V_{SD}$               | source-drain voltage                  | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$             |     | -   | 0.75     | 1        | V    |
| t <sub>rr</sub>        | reverse recovery time                 | $I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$          |     | -   | 36       | -        | ns   |
| Q <sub>r</sub>         | recovered charge                      | V <sub>DS</sub> = 25 V; <u>Fig. 16</u>                                                     | [1] | -   | 37       | -        | nC   |
| t <sub>a</sub>         | reverse recovery rise time            |                                                                                            |     | -   | 21       | -        | ns   |
| t <sub>b</sub>         | reverse recovery fall time            |                                                                                            |     | -   | 14       | -        | ns   |

#### [1] includes capacitive recovery

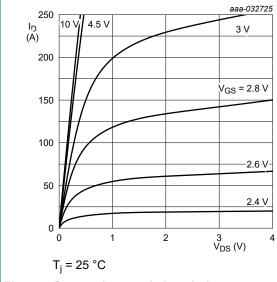


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

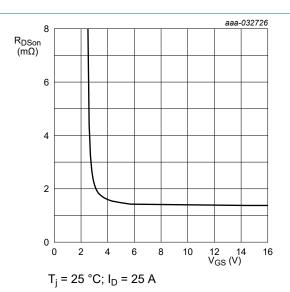


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

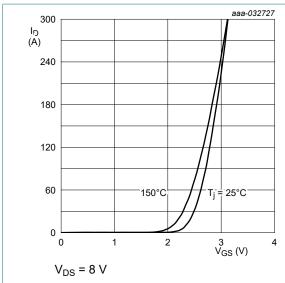


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

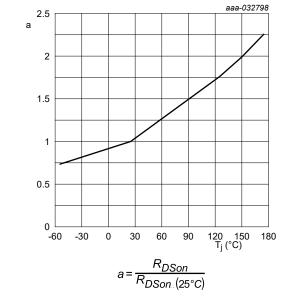


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

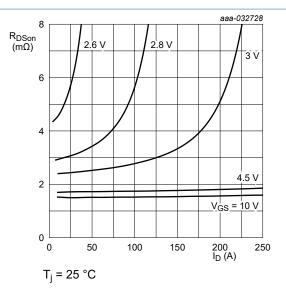


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

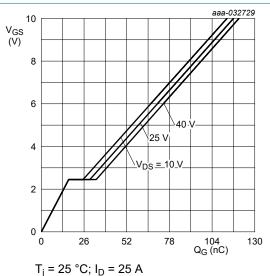


Fig. 12. Gate-source voltage as a function of gate charge; typical values

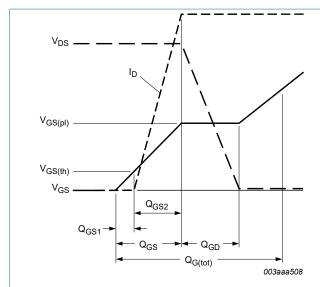


Fig. 13. Gate charge waveform definitions

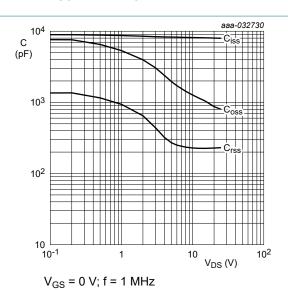


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

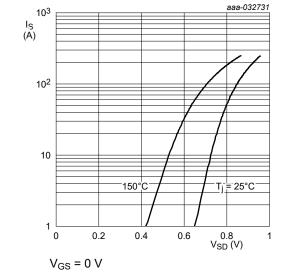


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

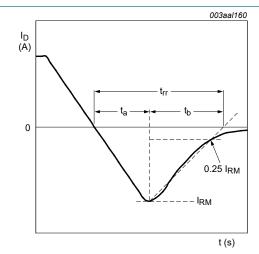
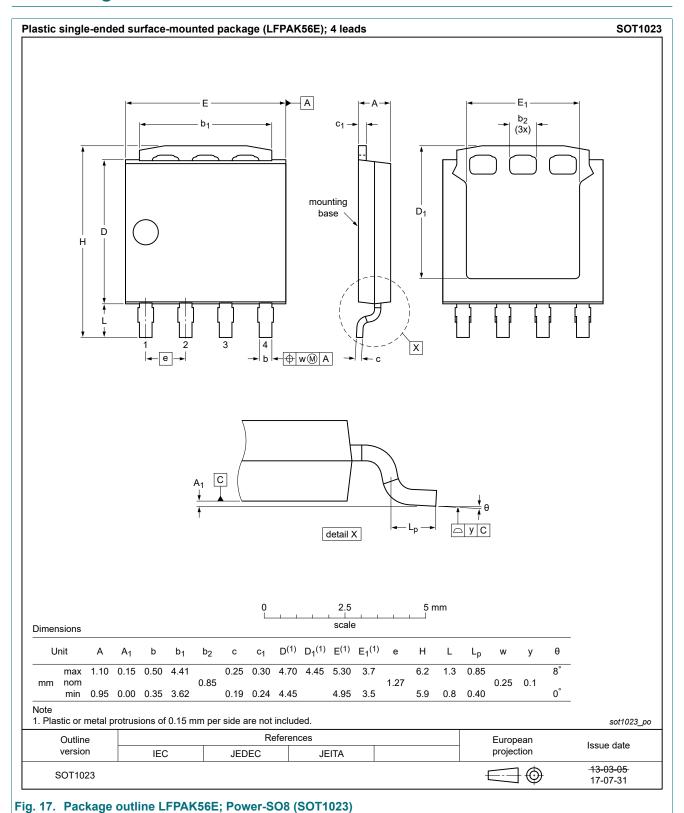
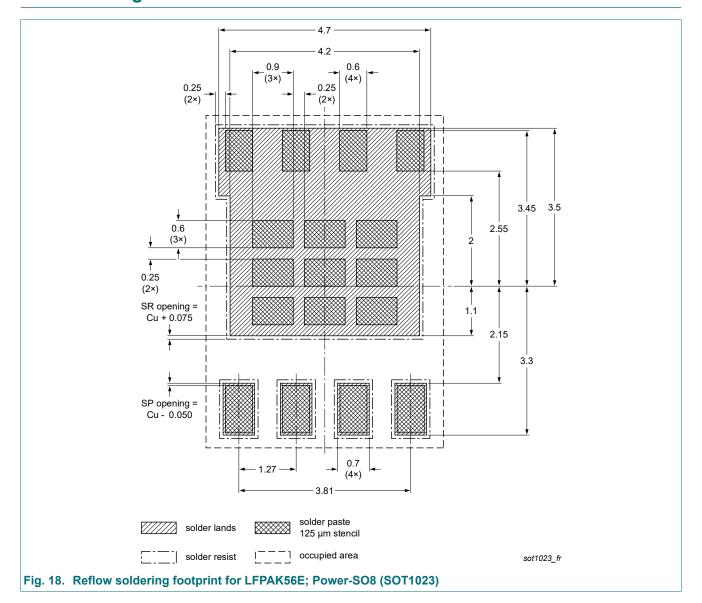


Fig. 16. Reverse recovery timing definition

# 11. Package outline



# 12. Soldering



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## 13. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition                                                                            |
|--------------------------------|-----------------------|---------------------------------------------------------------------------------------|
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| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

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